National Semiconductor

November 1995

MM54HC258/MM74HC258 Quad 2-Channel TRI-STATE® Multiplexer (Inverted Output)

General Description

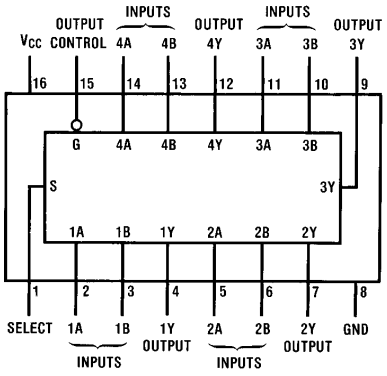
This Quad 2-to-1 line data selector/multiplexer utilizes advanced silicon-gate CMOS technology. Along with the high noise immunity and low power dissipation of standard CMOS integrated circuits, these possess the ability to drive LS-TT loads. The large output drive capability with the TRI-STATE feature make this device ideal for interfacing with bus lines in a bus organized system. When the Output Control line is taken high, the outputs of all four multiplexers are sent into a high impedance state. When the Output Control line is low, $\overline{A}$ or $\overline{B}$ data is selected for the HC258. The 54HC/74HC logic family is speed, function, and pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V_{CC} and ground.

Features

- Typical propagation delays: 16 ns
- Wide power supply range: 2V–6V
- Low quiescent supply current: 80 μA maximum (74HC Series)
- TRI-STATE outputs for connection to system buses
- Added circuitry allows data input levels to float during TRI-STATE with no additional power consumption

Connection Diagram

Dual-In-Line Package

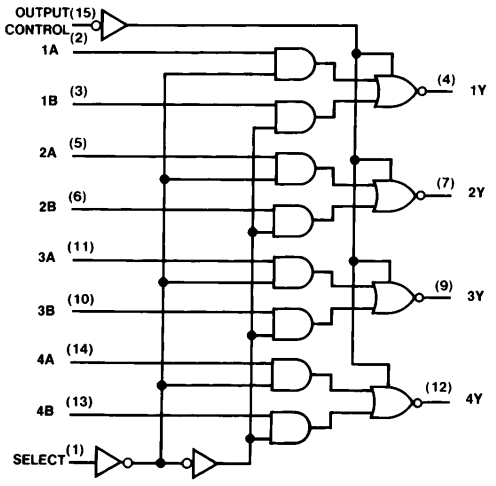


TL/F/9392–1

Top View

Order Number MM54HC258 or MM74HC258

Logic Diagram



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Truth Table

Inputs				Output Y
Output Control	Select	A	B	
H	X	X	X	Z
L	L	L	X	H
L	L	H	X	L
L	H	X	L	H
L	H	X	H	L

H = high level, L = low level, X = irrelevant, Z = high impedance, (off)

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RRD-B30M115/Printed in U. S. A.

Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage (V_{CC})	−0.5 to +7.0V
DC Input Voltage (V_{IN})	−1.5 to V_{CC} +1.5V
DC Output Voltage (V_{OUT})	−0.5 to V_{CC} +0.5V
Clamp Diode Current (I_{IK}, I_{OK})	±20 mA
DC Output Current, per pin (I_{OUT})	±35 mA
DC V_{CC} or GND Current, per pin (I_{CC})	±70 mA
Storage Temperature Range (T_{STG})	−65°C to +150°C
Power Dissipation (P_D) (Note 3)	600 mW
S.O. Package only	500 mW
Lead Temp. (T_L) (Soldering, 10 sec.)	260°C

Operating Conditions

	Min	Max	Units
Supply Voltage (V_{CC})	2	6	V
DC Input or Output Voltage (V_{IN}, V_{OUT})	0	V_{CC}	V
Operating Temp. Range (T_A)			
MM74HC	−40	+85	°C
MM54HC	−55	+125	°C
Input Rise or Fall Times (t_r, t_f) V_{CC} = 2.0V		1000	ns
V_{CC} = 4.5V		500	ns
V_{CC} = 6.0V		400	ns

DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	V_{CC}	T_A = 25°C	74HC T_A = −40 to 85°C	54HC T_A = −55 to 125°C	Units
				Typ	Guaranteed Limits		
V_{IH}	Minimum High Level Input Voltage		2.0V		1.5	1.5	1.5	V
			4.5V		3.15	3.15	3.15	V
			6.0V		4.2	4.2	4.2	V
V_{IL}	Maximum Low Level Input Voltage**		2.0V		0.5	0.5	0.5	V
			4.5V		1.35	1.35	1.35	V
			6.0V		1.8	1.8	1.8	V
V_{OH}	Minimum High Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20\ \mu A$	2.0V	2.0	1.9	1.9	1.9	V
			4.5V	4.5	4.4	4.4	4.4	V
			6.0V	6.0	5.9	5.9	5.9	V
		V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 6.0$ mA	4.5V	4.2	3.98	3.84	3.7	V
		$\|I_{OUT}\| \le 7.8$ mA	6.0V	5.7	5.48	5.34	5.2	V
V_{OL}	Maximum Low Level Output Voltage	V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 20\ \mu A$	2.0V	0	0.1	0.1	0.1	V
			4.5V	0	0.1	0.1	0.1	V
			6.0V	0	0.1	0.1	0.1	V
		V_{IN} = V_{IH} or V_{IL} $\|I_{OUT}\| \le 6.0$ mA	4.5V	0.2	0.26	0.33	0.4	V
		$\|I_{OUT}\| \le 7.8$ mA	6.0V	0.2	0.26	0.33	0.4	V
I_{IN}	Maximum Input Current	V_{IN} = V_{CC} or GND	6.0V		±0.1	±1.0	±1.0	μA
I_{OZ}	Maximum TRI-STATE Output Leakage	V_{OUT} = V_{CC} or GND OC = V_{IH}	6.0V		±0.5	±5.0	±10	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND I_{OUT} = 0 μA	6.0V		8.0	80	160	μA

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages (V_{OH}, and V_{OL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC} = 5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

**V_{IL} limits are currently tested at 20% of V_{CC}. The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics $V_{CC}=5V$, $T_A=25°C$, $t_r=t_f=6$ ns

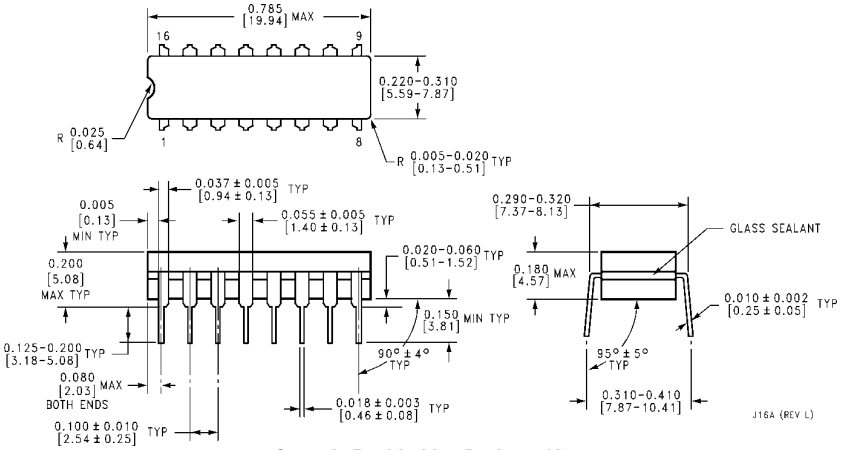
Symbol	Parameter	Conditions	Typ	Units
t_{PHL}, t_{PLH}	Maximum Propagation Delay, SELECT to any Y Output	$C_L=45$ pF	18	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, A or B to any Y Output	$C_L=45$ pF	16	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time, any Y Output to a Logic Level	$R_L=1$ kΩ $C_L=45$ pF	27	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time, any Y Output to a High Impedance State	$R_L=1$ kΩ $C_L=5$ pF	14	ns

AC Electrical Characteristics $V_{CC}=2.0V$ to $6.0V$, $C_L=50$ pF, $t_r=t_f=6$ ns (unless otherwise specified)

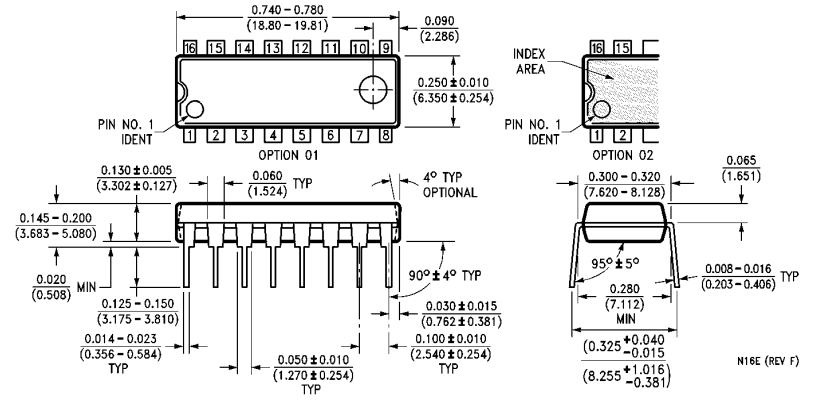
Symbol	Parameter	Conditions	V_{CC}	$T_A=25°C$	74HC $T_A=-40$ to $85°C$	54HC $T_A=-55$ to $125°C$	Units
				Typ	Guaranteed Limits		
t_{PHL}, t_{PLH}	Maximum Propagation Delay, SELECT to any Y Output	$C_L=50$ pF	2.0V		120	150	180	ns
		$C_L=50$ pF	4.5V	17	24	30	36	ns
		$C_L=50$ pF	6.0V		20	26	31	ns
t_{PHL}, t_{PLH}	Maximum Propagation Delay, A or B to any Y Output	$C_L=50$ pF	2.0V		90	115	135	ns
		$C_L=50$ pF	4.5V	14	18	23	27	ns
		$C_L=50$ pF	6.0V		15	20	23	ns
t_{PZH}, t_{PZL}	Maximum Output Enable Time, any Y Output to a Logic Level	$R_L=1$ kΩ						
		$C_L=50$ pF	2.0V		160	200	240	ns
		$C_L=50$ pF	4.5V	25	32	40	48	ns
		$C_L=50$ pF	6.0V		27	34	41	ns
t_{PHZ}, t_{PLZ}	Maximum Output Disable Time, any Y Output to a High Impedance State	$R_L=1$ kΩ $C_L=50$ pF	2.0V		120	150	180	ns
			4.5V	15	24	30	36	ns
			6.0V		20	26	31	ns
t_{THL}, t_{TLH}	Maximum Output Rise and Fall Time	$C_L=50$ pF	2.0V		60	75	90	ns
			4.5V	8	12	15	18	ns
			6.0V		10	13	15	ns
C_{PD}	Power Dissipation Capacitance (Note 5)	(per mux) Enable Disabled		44				pF
C_{IN}	Maximum Input Capacitance			5	10	10	10	pF

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D=C_{PD}\,V_{CC}^2\,f+I_{CC}\,V_{CC}$, and the no load dynamic current consumption, $I_S=C_{PD}\,V_{CC}\,f+I_{CC}$.

Physical Dimensions inches (millimeters)



Ceramic Dual-In-Line Package (J)
Order Number MM54HC258J or MM74HC258J
NS Package Number J16A



Molded Dual-In-Line Package (N)
Order Number MM74HC258N
NS Package Number N16E

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